

## Supporting information

### Enhancing ambipolar carrier transport of black phosphorus field-effect transistors with Ni-P alloy contacts

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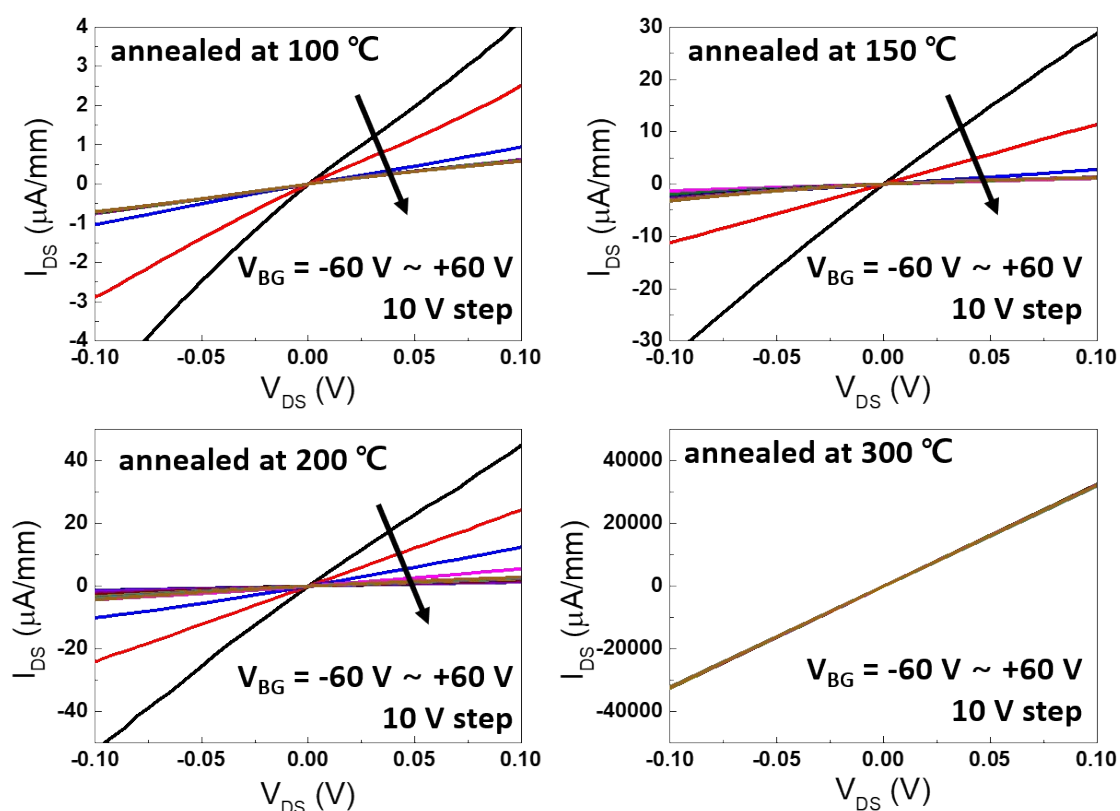


Figure S1 Output characteristics of BP FET after low-vacuum annealing at 100, 150, 200, and 300 °C.

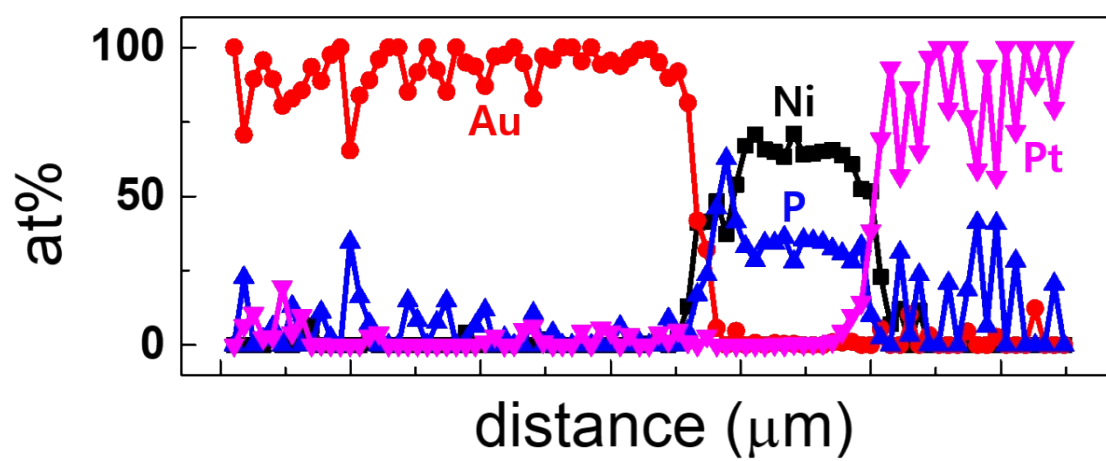


Figure S2 EDX atomic composition along the yellow line in Fig. 3(e)